



ENTERPRISE D-SERIES

MP-D100 PCIe Gen4 Data Center High-Speed Storage in M.2 and E1.S Form Factors

The MP-D100 has enterprise SSD firmware optimized for data center applications that supports a high Quality of Service (QoS) in command execution completion times. Miphi's business model is to customize the MP-D100 Series SSD platform to our customers' unique application and brand requirements making the Enterprise SSD truly unique to each partner.



Product Features

Miphi 4th Generation LDPC ECC Engine While flash memory cells deteriorate with use and can generate stored data bit errors, the MP-D100 utilizes Miphi's proprietary Low Density Parity Check error-correcting code algorithm to ensure robust data entry and extraction, as well as protection from internal corruption.

Market-leading Performance

Manufactured using TSMC's 12nm process technology, the D100 is optimized for a PCIe Gen4x4 interface, enabling SSDs with maximized bandwidths and link efficiency. Paired with state-of-the-art 3D NAND flash memory chips, the D100 handles application payloads immaculately with minimal latency.

PCIe Gen4x4 and Backward Compatibility

The D100 SSD is designed with the PCIe Gen4x4 interface and the NVMe 1.4 command specification, making it an excellent performance upgrade for PCIe Gen3 and Gen4 M.2 2280 slots.

Security Features

The MP-D100 supports the latest security and encryption standards defined byPyrite,AES256, SHA512, and RSA4096.



Solutions MP-D100P

| | | M.2 2280 | | | |
|--|---|---|---|---|-----------|
| | Capacity ⁽¹⁾ | 480GB | 960GB | 1920GB | - |
| | Sequential Read | 6000 MB/s | 6000 MB/s | 6000 MB/s | - |
| Performance ^(2,3) | Sequential Write | 700 MB/s | 1400 MB/s | 1800 MB/s | - |
| | 4K Random Read | 450K IOPS | 750K IOPS | 800K IOPS | - |
| | 4K Random Write | 25K IOPS | 50K IOPS | 60K IOPS | - |
| Power | Max | 8.5 W | 9.5 W | 11.0 W | - |
| Consumption ⁽⁴⁾ | Idle | 4 W | 4 W | 4.2 W | - |
| | Read latency | 75 us | 75 us | 75 us | - |
| Latency | Write latency | 40 us | 35 us | 35 us | - |
| | | M.2 2211 | 0 | | _ |
| | Capacity ⁽¹⁾ | 480GB | 960GB | 1920GB | 3840GB |
| Performance ^(2:3) | Sequential Read | 6000 MB/s | 6000 MB/s | 6000 MB/s | 4500 MB/ |
| | Sequential Write | 700 MB/s | 1400 MB/s | 1800 MB/s | 1700 MB/ |
| | 4K Random Read | 450K IOPS | 750K IOPS | 800K IOPS | 400K IOPS |
| | 4K Random Write | | | 60K IOPS | |
| | | 25K IOPS | 50K IOPS | | 40K IOPS |
| Power | Max | 8.5 W | 9.5 W | 11 W | 11.55 W |
| Consumption ⁽⁴⁾ | Idle | 8.5 W | 8.5 W | 8.5 W | 8.5 W |
| Latency | Read latency | 75 | 75 | 75 | 80 |
| | Write latency | 40 | 35 | 35 | 25 |
| | (1) | E1.S | 0(000 | 100000 | 204000 |
| | Capacity ¹⁾ | 480GB | 960GB | 1920GB | 3840GB |
| | Sequential Read | 6500 MB/s | 6800 MB/s | 6800 MB/s | 6800 MB/s |
| Performance ^(2,3) | Sequential Write | 700 MB/s | 1400 MB/s | 2000 MB/s | 1700 MB/s |
| | 4K Random Read | 450K IOPS | 800K IOPS | 900K IOPS | 650K IOPS |
| | 4K Random Write | 25K IOPS | 50K IOPS | 60K IOPS | 70K IOPS |
| Power Consumption ⁽⁴⁾ | Max | 9.5W | 10.5W | 13.5W | 12.5W |
| | Idle | 4 W | 4 W | 4.2 W | 4.2W |
| | | | 75 us | 75 us | 80 us |
| Latency | Read latency Write latency | 75 us | | | 25 110 |
| Latency | Write latency | 40 us | 30 us | 25 us | 25 us |
| Latency | Write latency | | 30 us | 25 us | 25 us |
| Latency | Write latency Interface | 40 us | 30 us PCle | 25 us 4.0x4 | 25 us |
| Latency | Write latency Interface NAND Flash | 40 us | 30 us PCle 3D | 25 us 4.0x4 TLC | 25 us |
| Latency | Write latency Interface NAND Flash DWPD ⁽⁵⁾ | 40 us | 30 us PCle 3D | 25 us 4.0x4 TLC 1 | 25 us |
| | Write latency Interface NAND Flash DWPD ⁽⁵⁾ UBER | 40 us | 30 us PCle 3D <1 se | 25 us 4.0x4 TLC 1 ector per 10 ⁷ bits read | 25 us |
| | Write latency Interface NAND Flash DWPD ⁽⁵⁾ UBER Operating Temperature | 40 us | 30 us PCle 3D < 1 se 0°C | 25 us 4.0x4 TLC 1 ector per 10 ¹² bits read 5 - 70°C | 25 us |
| | Write latency Interface NAND Flash DWPD ⁽⁵⁾ UBER | 40 us Features | 30 us PCle 3D <1 se 0°C -40°6 | 25 us 4.0x4 TLC 1 ector per 10 ⁷ bits read | 25 us |
| | Write latency Interface NAND Flash DWPD ⁽⁵⁾ UBER Operating Temperature | 40 us Features Key Featur | 30 us PCle 3D <1 se 0°C -40°6 | 25 us 4.0x4 TLC 1 ector per 10 ¹² bits read 5 - 70°C | 25 us |
| • LDPC • NVME 1.4 | Write latency Interface NAND Flash DWPD ⁽⁵⁾ UBER Operating Temperature operating temperature | 40 us Features Key Featur | 30 us PCle 3D < 1 se 0°C -40°(es TCG Opal 2.0 Sanitize | 25 us 4.0x4 TLC 1 ector per 10 ¹² bits read 5 - 70°C | 25 us |
| • Non - • LDPC | Write latency Interface NAND Flash DWPD ⁽⁵⁾ UBER Operating Temperature operating temperature | 40 us Features Key Featur | 30 us PCle 3D 3D 40°C -40°C es TCG Opal 2.0 | 25 us 4.0x4 TLC 1 ector per 10 ¹² bits read 5 - 70°C | 25 us |
| • LDPC • NVME 1.4 | Write latency Interface NAND Flash DWPD ⁽⁵⁾ UBER Operating Temperature operating temperature | 40 us Features Key Featur | 30 us PCle 3D 3D <1 se 0°C -40°C es TCG Opal 2.0 Sanitize NVME-MI | 25 us 4.0x4 TLC 1 ector per 10 ¹² bits read 5 - 70°C | 25 us |
| • LDPC • NVME 1.4 | Write latency Interface NAND Flash DWPD ⁽⁵⁾ UBER Operating Temperature operating temperature | 40 us Features Key Feature | 30 us PCle 3D 3D <1 se 0°C -40°t es TCG Opal 2.0 Sanitize NVME-MI (2280) | 25 us 4.0x4 TLC 1 ector per 10 ¹² bits read 5 - 70°C | 25 us |
| • • LDPC • NVME 1.4 • End-to-End Dat | Write latency Interface NAND Flash DWPD ⁽⁵⁾ UBER Operating Temperature operating temperature | 40 us Features Key Feature • • • • • | 30 us PCle 3D 3D <1 se 0°C -40°t es TCG Opal 2.0 Sanitize NVME-MI (2280) | 25 us 4.0x4 TLC 1 ector per 10 ⁷ bits read - 70°C C-85°C | 25 us |
| Non - • LDPC • NVME 1.4 • End-to-End Dat Non-SED | Write latency Interface NAND Flash DWPD ⁽⁵⁾ UBER Operating Temperature operating temperature | 40 us Features Key Feature • • • • • | 30 us PCle 3D <1 se 0°C -40°C es TCG Opal 2.0 Sanitize NVME-MI (2280) MPD100P960G-2280-N MPD100P960G-2280-S | 25 us 4.0x4 TLC 1 2.00°C 2.85°C 3.00° | 25 us |
| Non - • LDPC • NVME 1.4 • End-to-End Dat Non-SED | Write latency Interface NAND Flash DWPD ⁽⁵⁾ UBER Operating Temperature operating temperature | 40 us Features Key Feature | 30 us PCle 3D <1 se 0°C -40°C es TCG Opal 2.0 Sanitize NVME-MI (2280) MPD100P960G-2280-N MPD100P960G-2280-S | 25 us 4.0x4 TLC 1 2.00°C 2.85°C 3.00° | |

(1) 1 GB = 1,000,000,000 bytes.
(2) Sequential Performance is based on FIO on Linux, 128K, with QD=32, 1 worker, and test drive set as secondary.
(3) Random Performance is based on FIO on Linux, 4K data size, QD=32, 1 worker, 4K aligned.
(4) Power consumption is measured during the sequential read/write and random read/write operations performed by iometer with the conditions described in the conditions describ (2)(3).(5) The results of DWPD are obtained in compliance with JESD219A Standards.



The data within this specification is subject to change by Miphi without notice. Performance numbers may vary based on system configuration and testing conditions. Copyright © 2024 Miphi Semiconductors Private Limited. All rights reserved.